

In the Claims

Claims 1-88 are canceled.

89. [Currently Amended] A method of processing a wafer comprising:
receiving a wafer within a workpiece processing apparatus;
supporting the wafer using a workpiece holder of the workpiece processing apparatus;
coupling circuitry of the wafer with circuitry of the workpiece holder;
processing exposing the wafer within the workpiece processing apparatus to process conditions usable to form at least one semiconductor device; and
communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

90. [Previously Presented] The method in accordance with claim 89 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at a surface of the wafer and a surface of the workpiece holder.

91. [Previously Presented] The method in accordance with claim 89 wherein the receiving comprises receiving a semiconductive wafer.

92. [Currently Amended] The method in accordance with claim 89 further comprising altering the processing process conditions responsive to the communicating.

93. [Currently Amended] The method in accordance with claim 89 wherein the communicating comprises communicating during the processing of a production workpiece.

94. [Previously Presented] The method in accordance with claim 89 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

95. [Previously Presented] The method in accordance with claim 89 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

96. [Previously Presented] The method in accordance with claim 89 wherein the communicating comprises communicating the signals comprising information.

97. [Currently Amended] The method in accordance with claim 89 wherein the communicating comprises communicating the signals comprising information regarding the processing process conditions.

98. [Currently Amended] A method of processing a workpiece comprising:
receiving a first workpiece and a second workpiece within a workpiece processing apparatus configured to form a semiconductor device using the first workpiece;
processing the first workpiece within the workpiece processing apparatus to form the semiconductor device; and
communicating signals intermediate the second workpiece and the workpiece processing apparatus.

99. [Currently Amended] The method in accordance with claim 98 further comprising electrically coupling the second workpiece and the workpiece processing apparatus:

100. [Currently Amended] The method in accordance with claim 99 wherein the coupling comprises contacting circuitry of the second workpiece and circuitry of the apparatus.

101. [Currently Amended] The method in accordance with claim 98 further comprising:

supporting [[a]] the second workpiece using a workpiece holder of the workpiece processing apparatus; and

coupling circuitry of the second workpiece and circuitry of the workpiece holder at a surface of the second workpiece and a surface of the workpiece holder.

102. [Currently Amended] The method in accordance with claim 98 wherein the receiving comprises receiving the first workpiece comprising a semiconductive wafer.

103. [Previously Presented] The method in accordance with claim 98 further comprising altering the processing responsive to the communicating.

104. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating during the processing.

105. [Previously Presented] The method in accordance with claim 98 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

106. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information.

107. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information regarding the processing.

108. [Previously Presented] A method of communicating signals with respect to a wafer comprising:

- providing a workpiece holder;
- supporting a wafer using the workpiece holder;
- coupling circuitry of the wafer with circuitry of the workpiece holder; and
- communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

109. [Previously Presented] The method in accordance with claim 108 wherein the providing the wafer comprises providing a semiconductive wafer.

110. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at a surface of the wafer and a surface of the workpiece holder.

111. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

112. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating using an intermediate member.

113. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating the signals comprising information.

114. [Currently Amended] The method in accordance with claim 108 wherein the communicating comprises communicating the signals comprising information regarding processing of the wafer process conditions of a workpiece processing apparatus.

115. [Currently Amended] A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to ~~process a workpiece to form~~ a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece; and

receiving the signals within the workpiece processing apparatus from the workpiece.

116. [Previously Presented] The method in accordance with claim 115 further comprising coupling circuitry of the workpiece with circuitry of the workpiece processing apparatus.

117. [Previously Presented] The method in accordance with claim 116 wherein the coupling comprises contacting the circuitry of the workpiece with the circuitry of the workpiece processing apparatus.

118. [Previously Presented] The method in accordance with claim 116 further comprising breaking the coupling of the circuitry of the workpiece and the circuitry of the workpiece processing apparatus.

119. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder, and wherein the receiving comprises receiving using the workpiece holder.

120. [Previously Presented] The method in accordance with claim 119 further comprising coupling circuitry of the workpiece and circuitry of the workpiece holder at a surface of the workpiece and a surface of the workpiece holder.

121. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder and an intermediate member, and wherein the receiving comprises receiving using the workpiece holder and the intermediate member.

122. [Previously Presented] The method in accordance with claim 115 wherein the providing the workpiece comprises providing a semiconductive wafer.

123. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising information.

124. [Currently Amended] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising information regarding ~~processing of the workpiece~~ process conditions of the workpiece processing apparatus.

125. [New] The method in accordance with claim 89 wherein the circuitry of the wafer comprises an electrical coupling at a surface of the wafer.

126. [New] The method in accordance with claim 89 wherein the wafer comprises a calibration workpiece.

127. [New] The method in accordance with claim 89 further comprising originating the signals using the circuitry of the wafer.

128. [New] The method in accordance with claim 98 wherein the first workpiece comprises a production workpiece and the second workpiece comprises a calibration workpiece.

129. [New] The method in accordance with claim 108 wherein the supporting the wafer comprises supporting the wafer comprising a calibration workpiece.

130. [New] The method in accordance with claim 115 wherein the providing comprises providing the workpiece comprising a calibration workpiece.

131. [New] The method in accordance with claim 115 further comprises exposing the workpiece to process conditions configured to form the semiconductor device.

132. [New] The method in accordance with claim 131 wherein the workpiece processing apparatus is adapted to form the semiconductor device from a production workpiece.